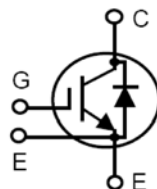


XPT™ 650V GenX3™ IXYN100N65C3H1

w/ Sonic Diode

Extreme Light Punch Through IGBT for 20-60kHz Switching



$$V_{CES} = 650V$$

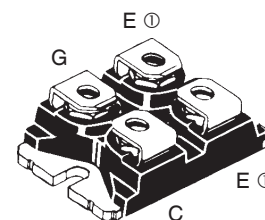
$$I_{C110} = 90A$$

$$V_{CE(sat)} \leq 2.3V$$

$$t_{fi(typ)} = 60ns$$

SOT-227B, miniBLOC

E153432



G = Gate, C = Collector, E = Emitter
 ① either emitter terminal can be used as Main or Kelvin Emitter

Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ C$ to $175^\circ C$	650	V
V_{CGR}	$T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$	650	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ C$	160	A
I_{C110}	$T_C = 110^\circ C$	90	A
I_{F110}	$T_C = 110^\circ C$	50	A
I_{CM}	$T_C = 25^\circ C$, 1ms	420	A
I_A	$T_C = 25^\circ C$	50	A
E_{AS}	$T_C = 25^\circ C$	600	mJ
SSOA	$V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 3\Omega$	$I_{CM} = 200$	A
(RBSOA)	Clamped Inductive Load	$V_{CE} \leq V_{CES}$	
t_{sc}	$V_{GE} = 15V$, $V_{CE} = 360V$, $T_J = 150^\circ C$	7	μs
(SCSOA)	$R_G = 10\Omega$, Non Repetitive		
P_C	$T_C = 25^\circ C$	600	W
T_J		-55 ... +175	$^\circ C$
T_{JM}		175	$^\circ C$
T_{stg}		-55 ... +175	$^\circ C$
V_{ISOL}	50/60Hz	$t = 1min$	2500 V~
	$I_{ISOL} \leq 1mA$	$t = 1s$	3000 V~
M_d	Mounting Torque		1.5/13 Nm/lb.in
	Terminal Connection Torque		1.3/11.5 Nm/lb.in
Weight		30	g

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- 2500V~ Isolation Voltage
- Anti-Parallel Sonic Diode
- Optimized for 20-60kHz Switching
- Square RBSOA
- Short Circuit Capability
- High Current Handling Capability

Advantages

- High Power Density
- Low Gate Drive Requirement

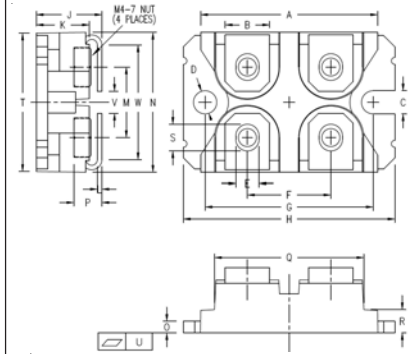
Applications

- Power Inverters
- UPS
- Motor Drives
- SMPS
- PFC Circuits
- Battery Chargers
- Welding Machines
- Lamp Ballasts
- High Frequency Power Inverters

Symbol	Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{CES}	$I_C = 250\mu A$, $V_{GE} = 0V$	650		V
$V_{GE(th)}$	$I_C = 250\mu A$, $V_{CE} = V_{GE}$	3.5		6.0 V
I_{CES}	$V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$			50 μA
				3 mA
I_{GES}	$V_{CE} = 0V$, $V_{GE} = \pm 20V$			± 100 nA
$V_{CE(sat)}$	$I_C = 70A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$		1.8	2.3 V
			2.2	V

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	$I_C = 60\text{A}, V_{CE} = 10\text{V}$, Note 1	30	55	S
C_{ies}	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		4800	pF
C_{oes}			475	pF
C_{res}			102	pF
$Q_{g(on)}$	$I_C = 100\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$		172	nC
Q_{ge}			30	nC
Q_{gc}			80	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 3\Omega$ Note 2		23	ns
t_{ri}			42	ns
E_{on}			1.30	mJ
$t_{d(off)}$			107	ns
t_{fi}			60	ns
E_{off}			0.83	mJ
$t_{d(on)}$	Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 50\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 400\text{V}, R_G = 3\Omega$ Note 2		24	ns
t_{ri}			38	ns
E_{on}			2.55	mJ
$t_{d(off)}$			134	ns
t_{fi}			66	ns
E_{off}			1.15	mJ
R_{thJC}			0.25	$^\circ\text{C/W}$
R_{thCS}		0.05		$^\circ\text{C/W}$

SOT-227B miniBLOC (IXYN)



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.489	1.505	37.80	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1
V	.130	.180	3.30	4.57
W	.780	.830	19.81	21.08

Reverse Sonic Diode (FRD)

Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified)		Characteristic Values		
		Min.	Typ.	Max.
V_F	$I_F = 100\text{A}, V_{GE} = 0\text{V}$, Note 1 $T_J = 150^\circ\text{C}$		1.7 1.8	V V
I_{RM}	$I_F = 100\text{A}, V_{GE} = 0\text{V}, T_J = 150^\circ\text{C},$ $-di_F/dt = 1500\text{A}/\mu\text{s}, V_R = 400\text{V}$		95	A
t_{rr}			100	ns
R_{thJC}				0.42 $^\circ\text{C/W}$

Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher $V_{CE}(\text{clamp})$, T_J or R_G .

PRELIMINARY TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

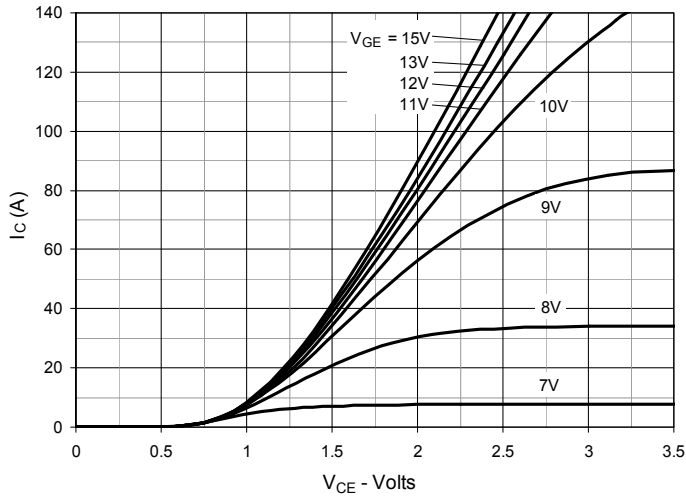


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

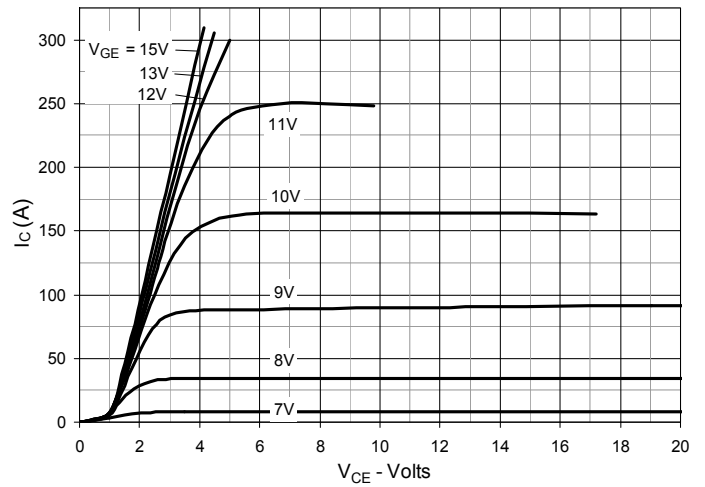


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

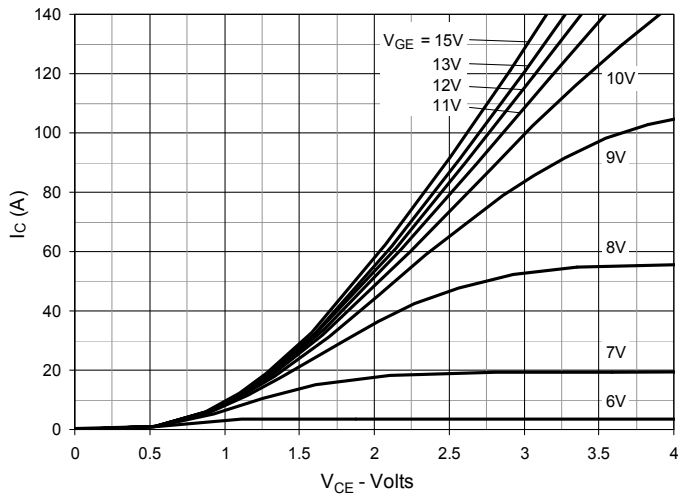


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

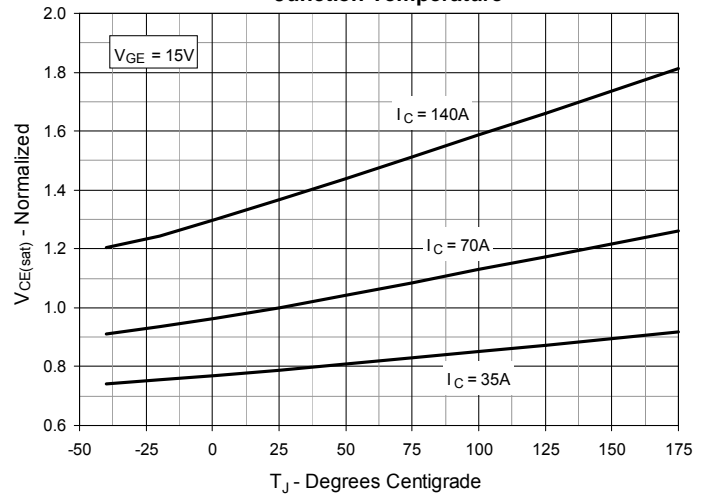


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

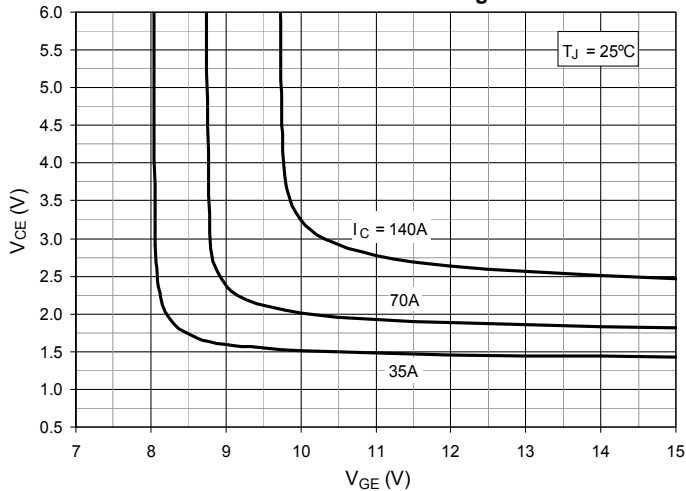


Fig. 6. Input Admittance

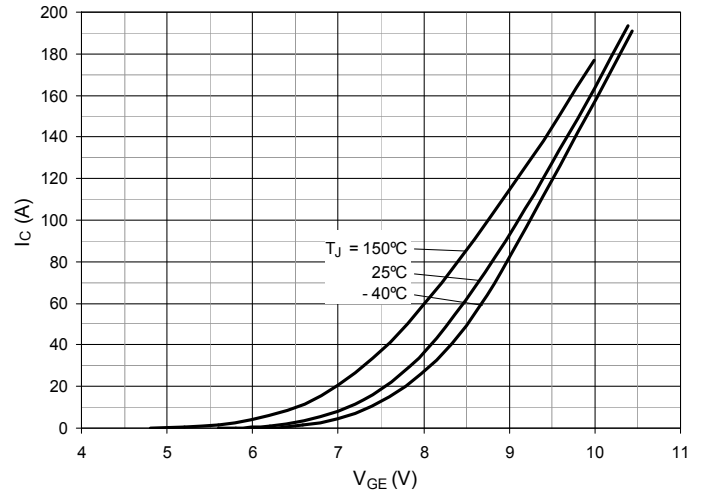


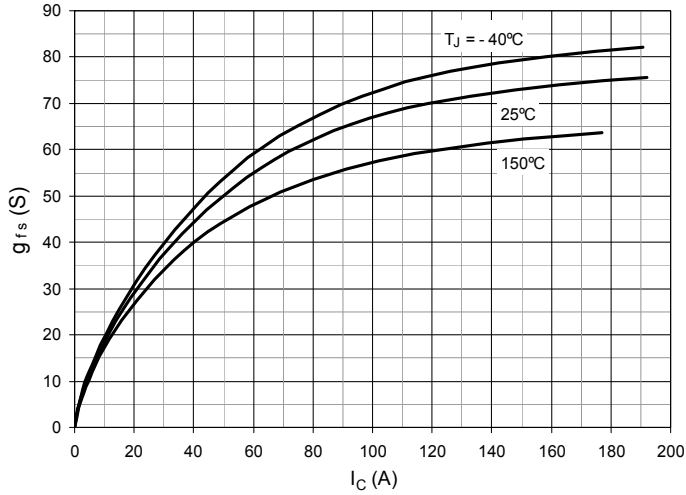
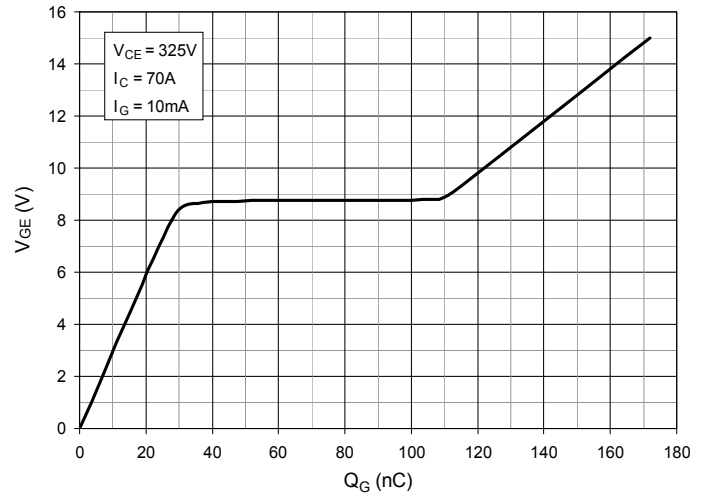
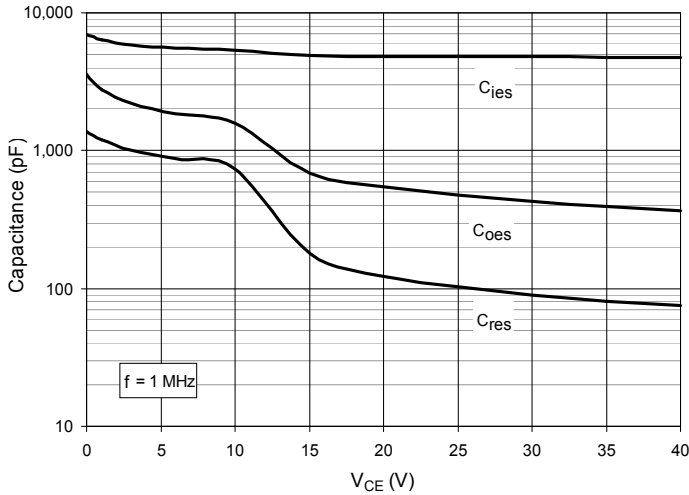
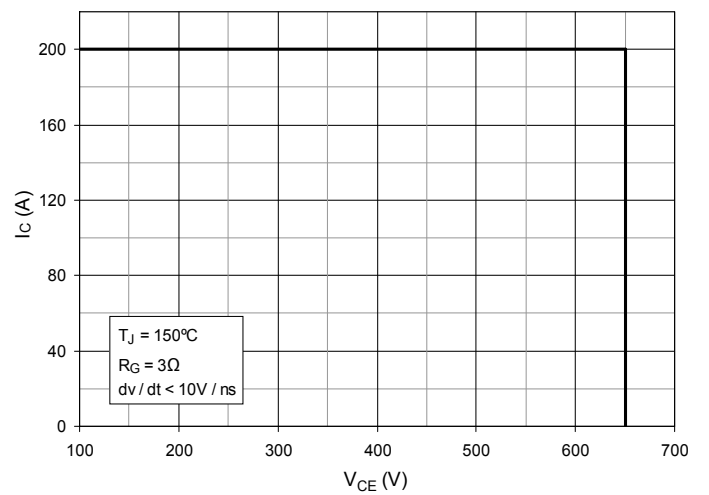
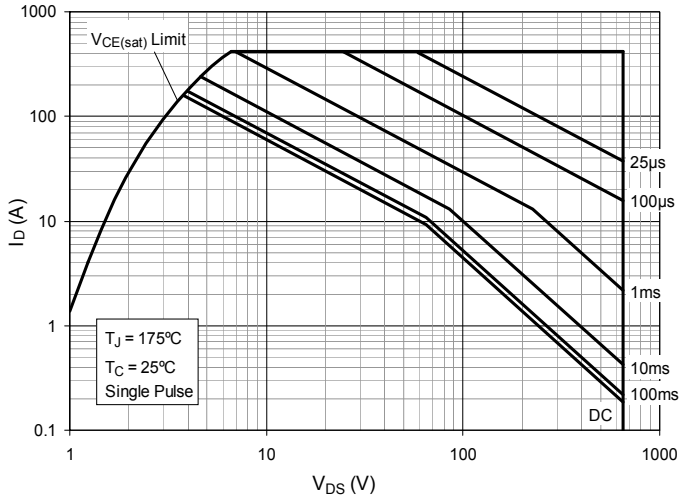
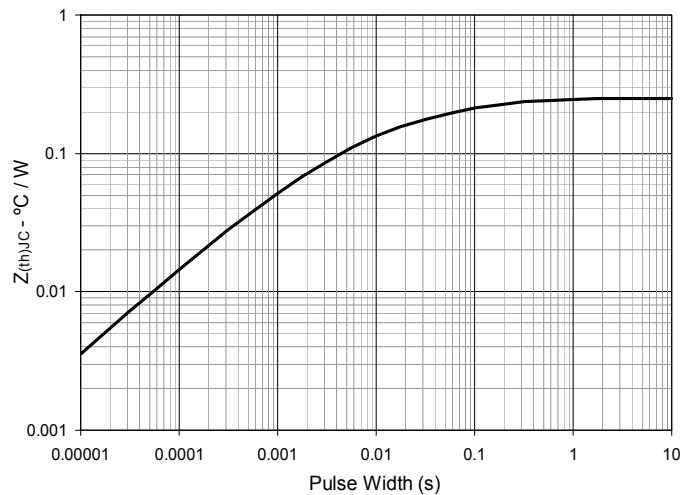
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Forward-Bias Safe Operating Area

Fig. 12. Maximum Transient Thermal Impedance (IGBT)


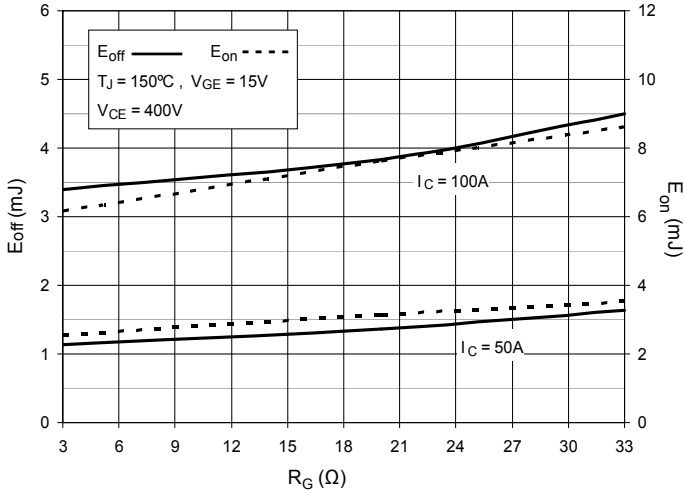
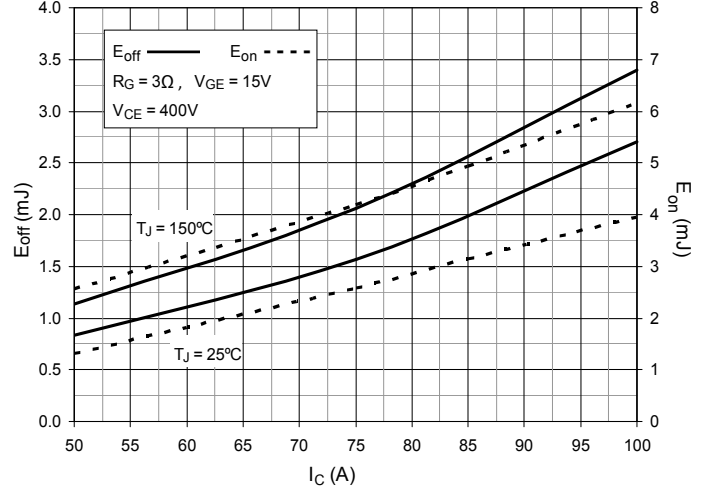
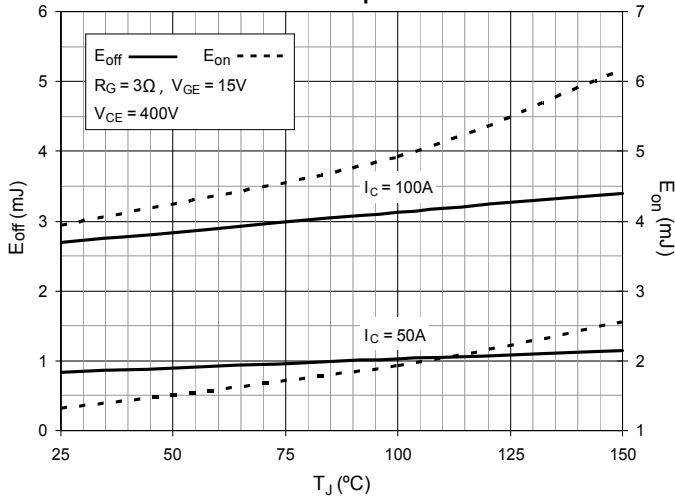
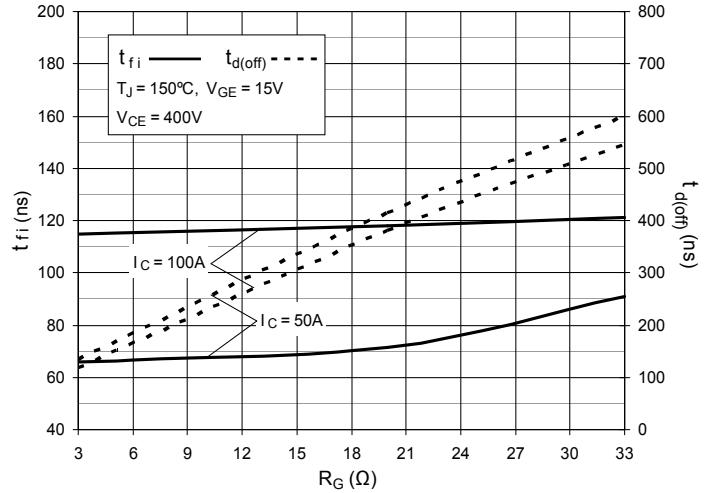
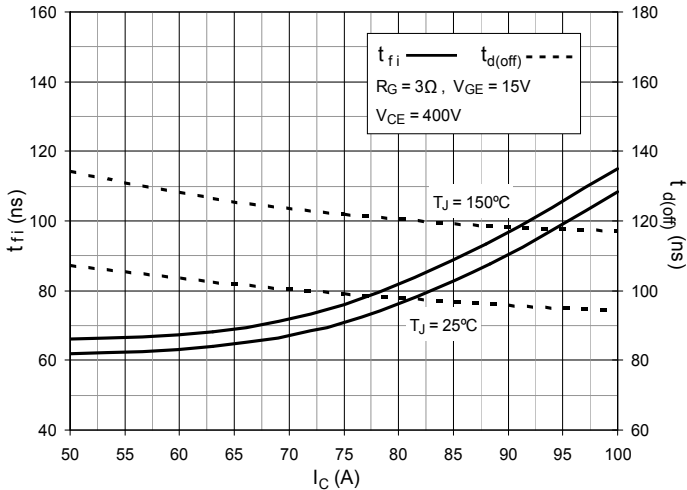
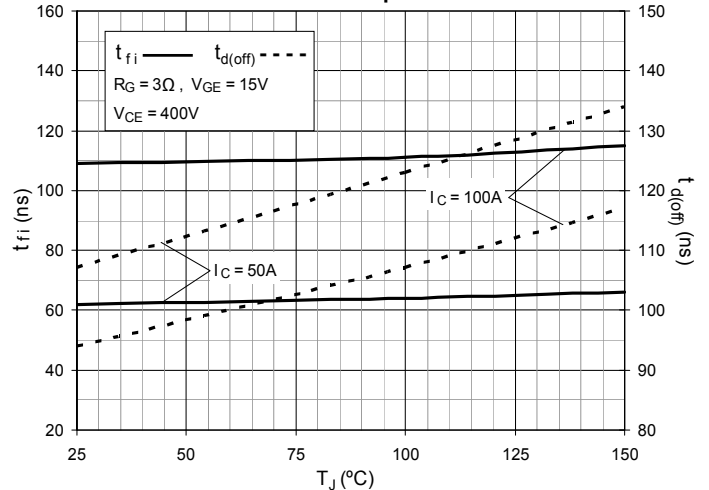
Fig. 13. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 14. Inductive Switching Energy Loss vs. Collector Current

Fig. 15. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 16. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 17. Inductive Turn-off Switching Times vs. Collector Current

Fig. 18. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 19. Inductive Turn-on Switching Times vs. Gate Resistance

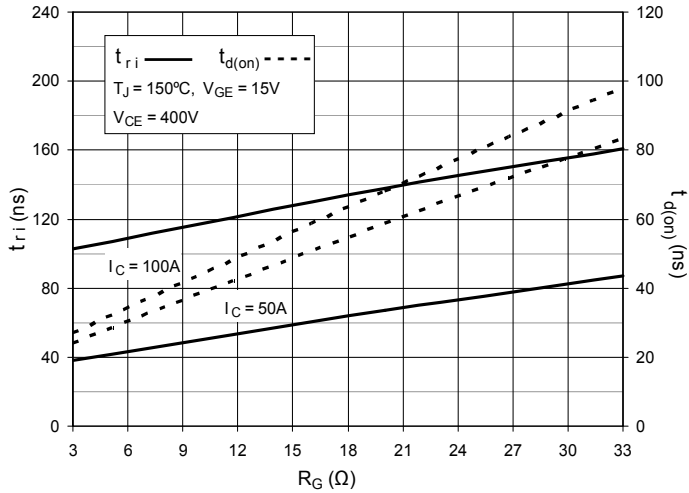


Fig. 20. Inductive Turn-on Switching Times vs. Collector Current

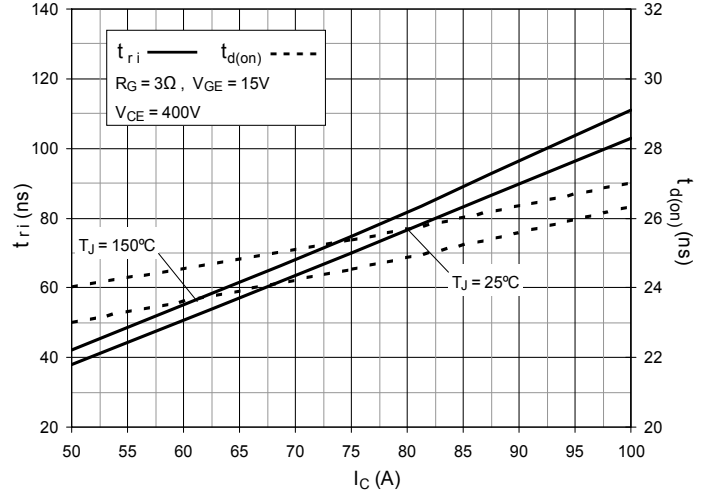


Fig. 21. Inductive Turn-on Switching Times vs. Junction Temperature



Fig. 22. Maximum Peak Load Current vs. Frequency

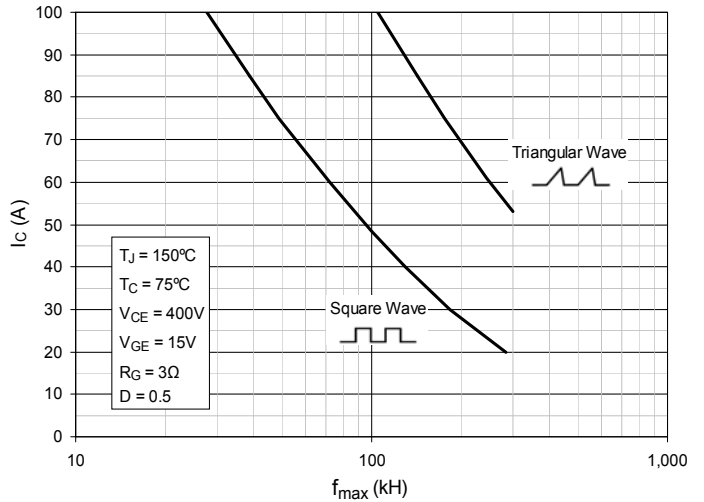


Fig. 23. Typ. Forward characteristics

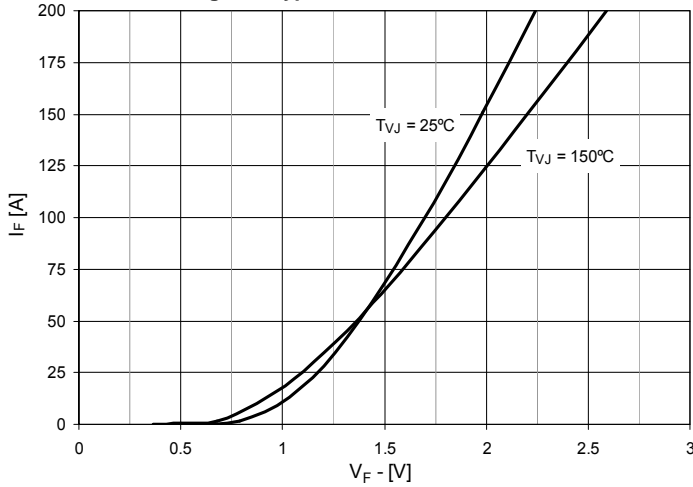


Fig. 24. Typ. Reverse Recovery Charge Q_{rr} vs. $-di_F/dt$

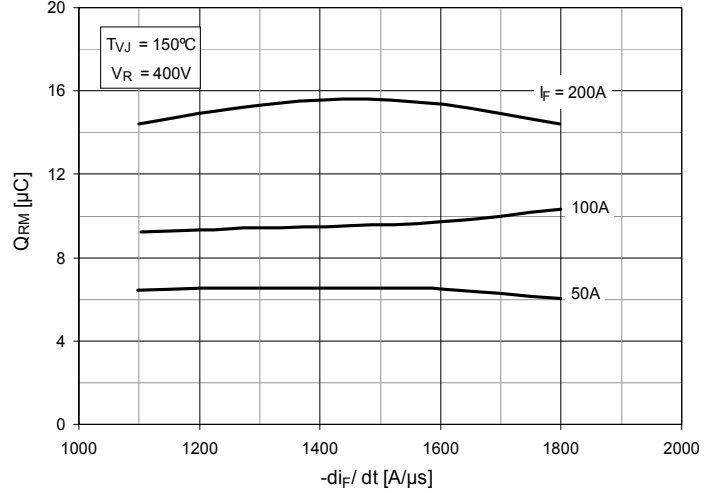


Fig. 25. Typ. Peak Reverse Current I_{RM} vs. $-di_F/dt$

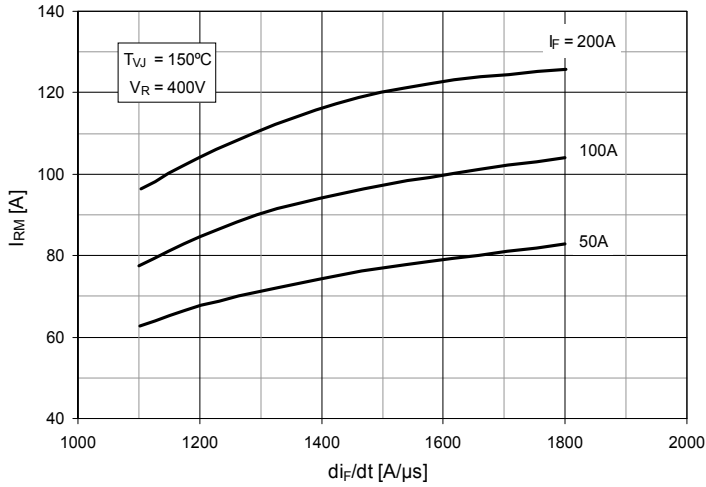


Fig. 26. Typ. Recovery Time t_{rr} vs. $-di_F/dt$

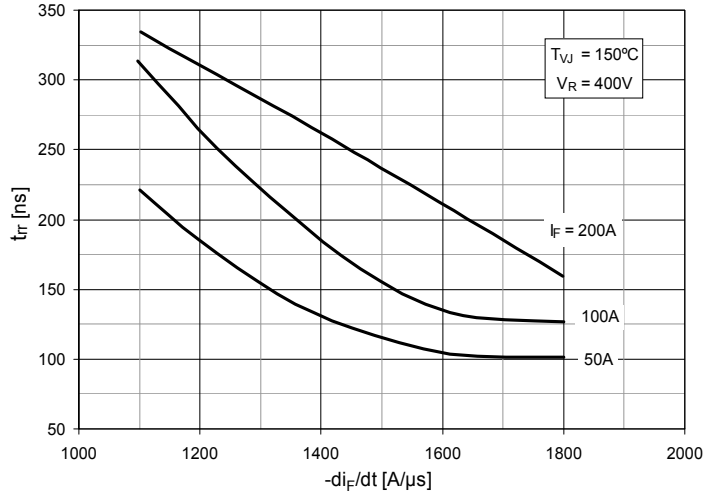


Fig. 27. Typ. Recovery Energy E_{rec} vs. $-di_F/dt$

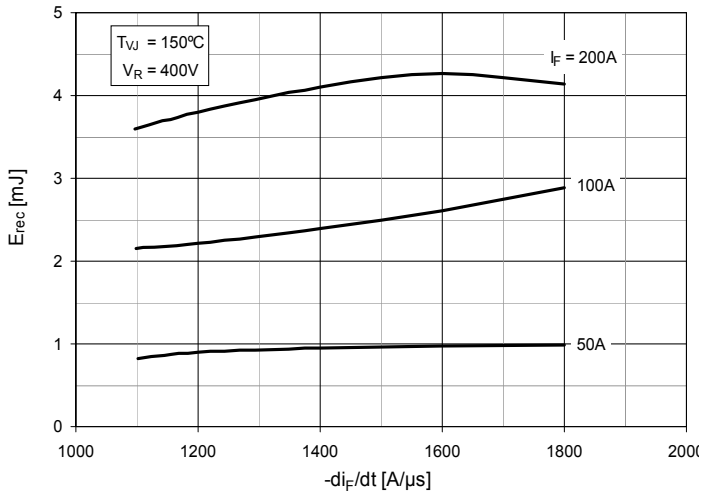


Fig. 28. Maximum Transient Thermal Impedance (Diode)

